

# Sergiy Krylyuk

## List of Publications by Year in descending order

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75  
papers

2,319  
citations

331670

21  
h-index

214800

47  
g-index

77  
all docs

77  
docs citations

77  
times ranked

4767  
citing authors

#	ARTICLE	IF	CITATIONS
1	In situ atomic-scale imaging of electrochemical lithiation in silicon. <i>Nature Nanotechnology</i> , 2012, 7, 749-756.	31.5	533
2	Electric-field induced structural transition in vertical MoTe <sub>2</sub> - and Mo <sub>1-x</sub> W <sub>x</sub> Te <sub>2</sub> -based resistive memories. <i>Nature Materials</i> , 2019, 18, 55-61.	27.5	300
3	Characterization of Few-Layer 1T <sup>±</sup> MoTe <sub>2</sub> by Polarization-Resolved Second Harmonic Generation and Raman Scattering. <i>ACS Nano</i> , 2016, 10, 9626-9636.	14.6	148
4	Electrolyte Stability Determines Scaling Limits for Solid-State 3D Li Ion Batteries. <i>Nano Letters</i> , 2012, 12, 505-511.	9.1	121
5	Photocurrent detection of the orbital angular momentum of light. <i>Science</i> , 2020, 368, 763-767.	12.6	113
6	Tapering Control of Si Nanowires Grown from SiCl <sub>4</sub> at Reduced Pressure. <i>ACS Nano</i> , 2011, 5, 656-664.	14.6	85
7	Ultimate Bending Strength of Si Nanowires. <i>Nano Letters</i> , 2012, 12, 2599-2604.	9.1	74
8	The structural phases and vibrational properties of Mo <sub>1-x</sub> W <sub>x</sub> Te <sub>2</sub> alloys. <i>2D Materials</i> , 2017, 4, 045008.	4.4	65
9	Hexagonal MoTe <sub>2</sub> with Amorphous BN Passivation Layer for Improved Oxidation Resistance and Endurance of 2D Field Effect Transistors. <i>Scientific Reports</i> , 2018, 8, 8668.	3.3	61
10	Probing the Optical Properties and Strain-Tuning of Ultrathin Mo <sub>1-x</sub> W <sub>x</sub> Te <sub>2</sub> . <i>Nano Letters</i> , 2018, 18, 2485-2491.	9.1	53
11	Electron Microscopy Observation of TiO <sub>2</sub> Nanocrystal Evolution in High-Temperature Atomic Layer Deposition. <i>Nano Letters</i> , 2013, 13, 5727-5734.	9.1	49
12	Nanoscale Heterogeneities in Monolayer MoSe <sub>2</sub> Revealed by Correlated Scanning Probe Microscopy and Tip-Enhanced Raman Spectroscopy. <i>ACS Applied Nano Materials</i> , 2018, 1, 572-579.	5.0	45
13	Surface effects on the elastic modulus of Te nanowires. <i>Applied Physics Letters</i> , 2008, 92, 241908.	3.3	40
14	Compressive Stress Effect on the Radial Elastic Modulus of Oxidized Si Nanowires. <i>Nano Letters</i> , 2010, 10, 2031-2037.	9.1	38
15	Selective streptavidin bioconjugation on silicon and silicon carbide nanowires for biosensor applications. <i>Journal of Materials Research</i> , 2013, 28, 68-77.	2.6	30
16	Bending manipulation and measurements of fracture strength of silicon and oxidized silicon nanowires by atomic force microscopy. <i>Journal of Materials Research</i> , 2012, 27, 562-570.	2.6	29
17	Phonon anharmonicity in bulk <i>Td</i> -MoTe <sub>2</sub> . <i>Applied Physics Letters</i> , 2016, 109, .	3.3	27
18	Localized Excitons in NbSe <sub>2</sub> -MoSe <sub>2</sub> Heterostructures. <i>ACS Nano</i> , 2020, 14, 8528-8538.	14.6	26

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19	Substrate-mediated hyperbolic phonon polaritons in MoO <sub>3</sub> . Nanophotonics, 2021, 10, 1517-1527.	6.0	25
20	Nanowire Aptasensors for Electrochemical Detection of Cell-Secreted Cytokines. ACS Sensors, 2017, 2, 1644-1652.	7.8	24
21	Rapid thermal oxidation of silicon nanowires. Applied Physics Letters, 2009, 94, .	3.3	21
22	Formation of large-area GaN nanostructures with controlled geometry and morphology using top-down fabrication scheme. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2012, 30, .	1.2	20
23	Comprehensive optical characterization of atomically thin $\text{NbSe}_2$ . Physical Review B, 2018, 98, .	2.0	20
24	Nanostructures on SiC surface created by laser microablation. Applied Surface Science, 2008, 254, 2031-2036.	6.1	19
25	Contact-resonance atomic force microscopy for nanoscale elastic property measurements: Spectroscopy and imaging. Ultramicroscopy, 2009, 109, 929-936.	1.9	19
26	Characterization of deep-levels in silicon nanowires by low-frequency noise spectroscopy. Applied Physics Letters, 2011, 99, 113107.	3.3	19
27	Miniature all-solid-state heterostructure nanowire Li-ion batteries as a tool for engineering and structural diagnostics of nanoscale electrochemical processes. Nanoscale, 2014, 6, 11756-11768.	5.6	19
28	Automated Mechanical Exfoliation of MoS <sub>2</sub> and MoTe <sub>2</sub> Layers for Two-Dimensional Materials Applications. IEEE Nanotechnology Magazine, 2019, 18, 144-148.	2.0	18
29	Detection of Deep-Level in Doped Silicon Nanowires Using Low-Frequency Noise Spectroscopy. IEEE Transactions on Electron Devices, 2013, 60, 4206-4212.	3.0	17
30	Enhancement of the photoluminescence intensity in short-period GaAs/AlAs superlattices with different well and barrier thickness. Applied Physics Letters, 1999, 74, 2596-2598.	3.3	16
31	Enhancement of electron-phonon interaction in ultrashort-period GaAs/AlAs superlattices. Physical Review B, 1997, 55, 10621-10624.	3.2	15
32	Correlation between the performance and microstructure of Ti/Al/Ti/Au Ohmic contacts to p-type silicon nanowires. Nanotechnology, 2011, 22, 075206.	2.6	15
33	Large-area GaN n-core/p-shell arrays fabricated using top-down etching and selective epitaxial overgrowth. Applied Physics Letters, 2012, 101, .	3.3	15
34	Doping of MoTe <sub>2</sub> via Surface Charge Transfer in Air. ACS Applied Materials & Interfaces, 2020, 12, 18182-18193.	8.0	15
35	Mobility Extraction in 2D Transition Metal Dichalcogenide Devices—Avoiding Contact Resistance Implicated Overestimation. Small, 2021, 17, e2100940.	10.0	14
36	Dense nanoimprinted silicon nanowire arrays with passivated axial p-i-n junctions for photovoltaic applications. Journal of Applied Physics, 2015, 117, .	2.5	11

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37	Electrochemical Detection of Acetaminophen with Silicon Nanowires. <i>Electroanalysis</i> , 2018, 30, 886-891.	2.9	11
38	Observation of stimulated emission in an ultrashort-period nonsymmetric GaAs/AlAs superlattice. <i>Applied Physics Letters</i> , 2001, 78, 4085-4087.	3.3	10
39	Rapid determination of nanowires electrical properties using a dielectrophoresis-well based system. <i>Applied Physics Letters</i> , 2017, 110, .	3.3	10
40	Valley phenomena in the candidate phase change material WSe <sub>2</sub> (1-x)Te <sub>2</sub> x. <i>Communications Physics</i> , 2020, 3, .	5.3	10
41	Gamma-radiation effect on donor and acceptor states in CdTe and CdTe:Cl. <i>Journal of Alloys and Compounds</i> , 2004, 371, 142-145.	5.5	9
42	Near-theoretical fracture strengths in native and oxidized silicon nanowires. <i>Nanotechnology</i> , 2016, 27, 31LT02.	2.6	8
43	MoS <sub>2</sub> cleaning by acetone and UV-ozone: Geological and synthetic material. <i>Applied Surface Science</i> , 2019, 478, 183-188.	6.1	8
44	Thermomagnetic properties of $\text{Bi}_{24}\text{Mn}_{18}$ single crystal in the temperature range from 55 ÅK to 380 K. <i>Physical Review Materials</i> , 2021, 5, .		
45	Buffer layer engineering of L1 FePd thin films with large perpendicular magnetic anisotropy. <i>AIP Advances</i> , 2021, 11, .	1.3	8
46	Influence of layer deformation on thermal quenching of exciton photoluminescence in short-period GaAs/AlAs superlattices. <i>Semiconductor Science and Technology</i> , 2004, 19, 475-479.	2.0	7
47	Electrical properties and low-temperature photoluminescence of Si-doped CdTe crystals. <i>Semiconductors</i> , 2006, 40, 143-147.	0.5	7
48	Polarization effects in semiconductor superlattices. <i>Semiconductor Science and Technology</i> , 1995, 10, 422-424.	2.0	6
49	Charge density wave activated excitons in TiSe <sub>2</sub> /MoSe <sub>2</sub> heterostructures. <i>APL Materials</i> , 2022, 10, .	5.1	6
50	Spatially Resolved Band Gap and Dielectric Function in Two-Dimensional Materials from Electron Energy Loss Spectroscopy. <i>Journal of Physical Chemistry A</i> , 2022, 126, 1255-1262.	2.5	6
51	Comparable Enhancement of TERS Signals from WSe <sub>2</sub> on Chromium and Gold. <i>Journal of Physical Chemistry C</i> , 2020, 124, 8971-8977.	3.1	5
52	Development of a high-temperature (295-900 ÅK) Seebeck coefficient Standard Reference Material. <i>Journal of Materials Research</i> , 2021, 36, 3339-3352.	2.6	5
53	Structural and optical nanoscale analysis of GaN core-shell microrod arrays fabricated by combined top-down and bottom-up process on Si(111). <i>Japanese Journal of Applied Physics</i> , 2016, 55, 05FF02.	1.5	4
54	In Situ Transport Measurements Reveal Source of Mobility Enhancement of MoS <sub>2</sub> and MoTe <sub>2</sub> during Dielectric Deposition. <i>ACS Applied Electronic Materials</i> , 2020, 2, 1273-1279.	4.3	4

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55	Near-infrared photonic phase-change properties of transition metal ditellurides. , 2019, , .		4
56	Faceting control in core-shell GaN micropillars using selective epitaxy. APL Materials, 2014, 2, 106104.	5.1	3
57	Dielectric Properties of Nb <sub>x</sub> W <sub>1-x</sub> Se <sub>2</sub> Alloys. Journal of Research of the National Institute of Standards and Technology, 2019, 124, 1-10.	1.2	3
58	Control of polarity in multilayer MoTe <sub>2</sub> field-effect transistors by channel thickness. , 2018, 10725, .		3
59	Characterization of ultrashort-period GaAs/AlAs superlattices by exciton photoluminescence. Materials Science and Engineering C, 2002, 19, 439-443.	7.3	2
60	Biofunctionalization of Si nanowires using a solution based technique. Proceedings of SPIE, 2012, , .	0.8	2
61	Effect of Oblique Versus Normal Deposition on the Properties of Perpendicularly Magnetized FePd Thin Films. IEEE Magnetics Letters, 2020, 11, 1-5.	1.1	2
62	Low barrier height in a ZnO nanorods/NbSe <sub>2</sub> heterostructure prepared by van der Waals epitaxy. APL Materials, 2021, 9, .	5.1	2
63	Realization of vertically-aligned GaN n-p core-shell nanoscale structures using top-down fabrication. , 2011, , .		1
64	Real-time electrical detection of the formation and destruction of lipid bilayers on silicon nanowire devices. Sensing and Bio-Sensing Research, 2015, 4, 103-108.	4.2	1
65	Novel nanofluidic chemical cells based on self-assembled solid-state SiO <sub>2</sub> nanotubes. Nanotechnology, 2017, 28, 435601.	2.6	1
66	Automatic detection of crystallographic defects in STEM images by unsupervised learning with translational invariance. Microscopy and Microanalysis, 2021, 27, 1460-1462.	0.4	1
67	Correlated structural and optical properties of the MoTe <sub>2</sub> -WTe <sub>2</sub> alloy system (Conference) Tj ETQq1 1 0.784314 rgBT /Overlock 10 T		1
68	Valley phenomena in the candidate phase change material WSeTe. Communications Physics, 2020, 3, .	5.3	1
69	Time-resolved spectra and kinetics of the exciton photoluminescence in different types of GaAs/AlAs superlattices. Superlattices and Microstructures, 2001, 29, 57-66.	3.1	0
70	Electronic Characteristics of MoSe <sub>2</sub> and MoTe <sub>2</sub> for Nanoelectronic Applications. , 2018, , .		0
71	Investigation of Structural Phases in Mo <sub>1-x</sub> W <sub>x</sub> Te <sub>2</sub> in STEM. Microscopy and Microanalysis, 2020, 26, 2362-2364.	0.4	0
72	Electrochemical Detection of Acetaminophen with Silicon Nanowires. Electroanalysis, 2018, 30, .	2.9	0

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73	Rapid determination of nanowire electrical properties using a dielectrophoresis-well based system. Applied Physics Letters, 2017, 110, .	3.3	0
74	Near-infrared photonic phase-change properties of transition metal ditellurides. Proceedings of SPIE, 2019, 11085, .	0.8	0
75	Electrochemically Assaying Dopamine with p-Doped Silicon Nanowires. Analytical Letters, 0, , 1-9.	1.8	0